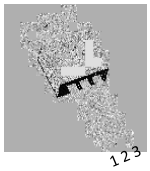
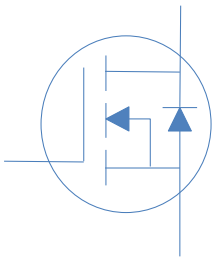
60V N-Ch Power MOSFET

V_{DS}		60	V
$R_{DS(on),typ}$	V_{GS}=10V	3.9	mΩ
$R_{DS(on),typ}$	V_{GS}=4.5V	5.3	mΩ
$R_{DS(on),typ}$	V_{GS}=10V	4.1	mΩ
$R_{DS(on),typ}$	V_{GS}=4.5V	5.6	mΩ
$I_{D\ (Sillicon\ Limited)}$		105	A





Part Number	Package	Marking
HGB053N06SL	TO-263	GB053N06SL
HGP053N06SL	TO-220	GP053N06SL

Absolute Maximum Ratings at T_j

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C	105	A
		T_C	74	
Drain to Source Voltage	V_{DS}	-	60	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	250	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C	80	mJ
Power Dissipation	P_D	T_C	125	
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	46	
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.2	

Electrical Characteristics at T_j

Static Characteristics

Parameter	Symbol	Conditions		Value			Unit
				min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA		60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA		1.0	1.6	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=60V, T_j		-	-	1	μA
		V_{GS}=0V, V_{DS}=60V, T_j		-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V		-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	TO-263	-	3.9	5	mΩ
		V_{GS}=4.5V, I_D=20A	TO-263	-	5.3	7.2	mΩ
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	TO-220	-	4.1	5.3	mΩ
		V_{GS}=4.5V, I_D=20A	TO-220	-	5.6	7.5	mΩ
Transconductance	g	V_{DS}=5V, I_D=20A		-	48	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS}		-	1.5	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}	-	2274	-	pF
Output Capacitance	C_{oss}		-	793	-	
	C_{rss}		-	35	-	
Total Gate Charge	Q_g(10V)	V_{DD}=30V, I_D=20A, V_{GS}=10V	-	36	-	nC
Total Gate Charge	Q_g(4.5V)		-	18	-	
Gate to Source Charge	Q_{gs}		-	4.5	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	7.5	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=30V, I_D=20A, V_{GS}=10V, R_G=10Ω,	-	11	-	ns
Rise time	t_r		-	7	-	
	t		-	35	-	
Fall Time	t		-	10	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=30V, I_F=20A, dI_F μs	-	30	-	ns
Reverse Recovery Charge	Q_{rr}		-	53	-	nC

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

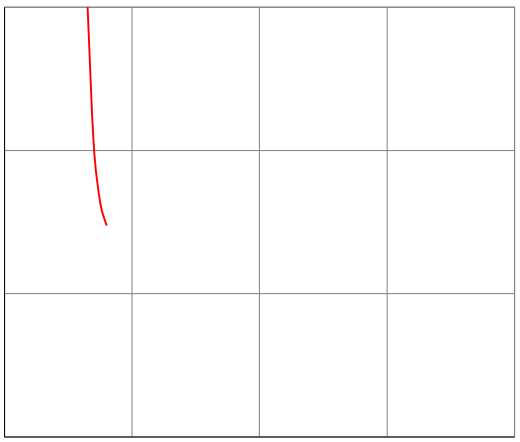
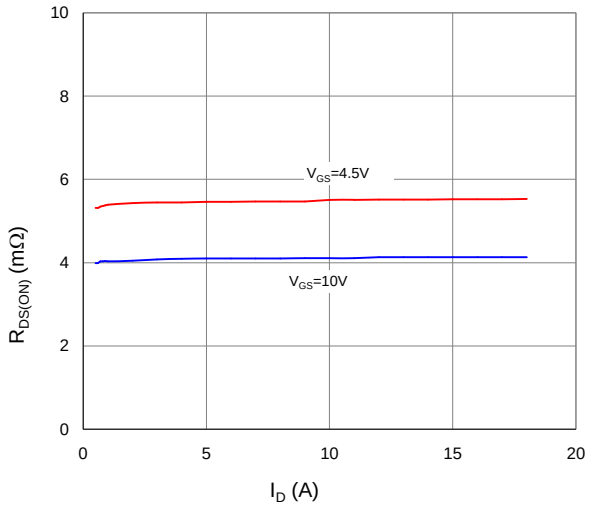


Figure 3. On-Resistance vs. Drain Current and Gate Voltage



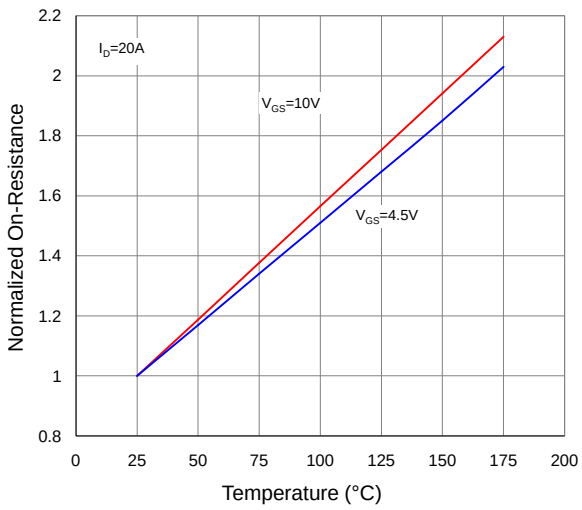


Figure 6. Typical Source-Drain Diode Forward Voltage

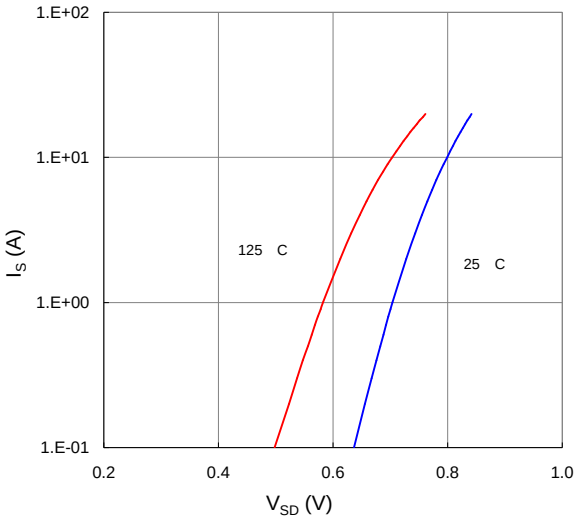


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

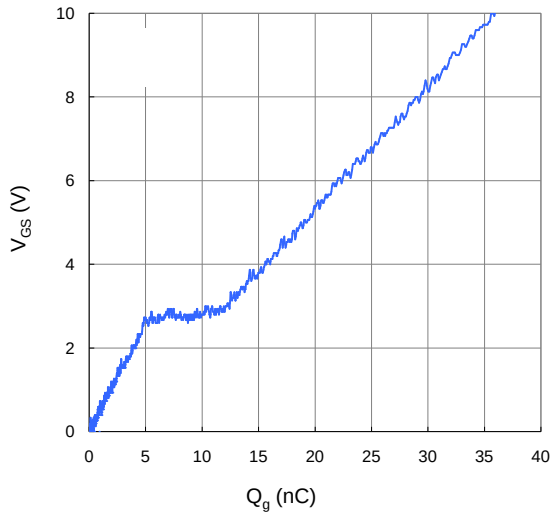
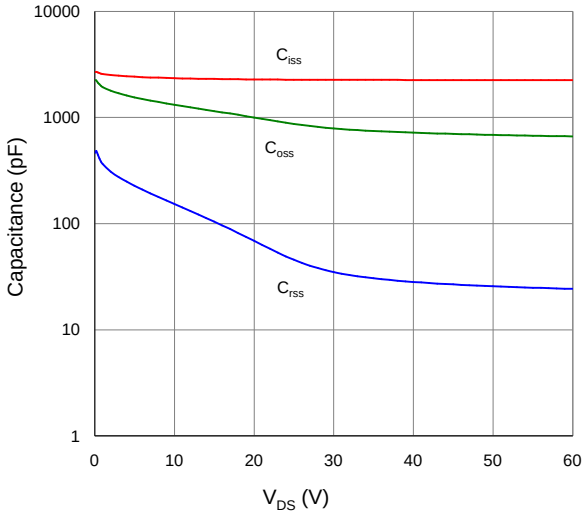


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage



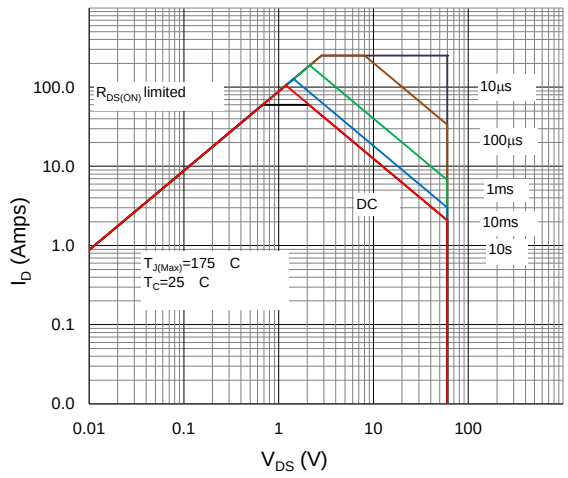
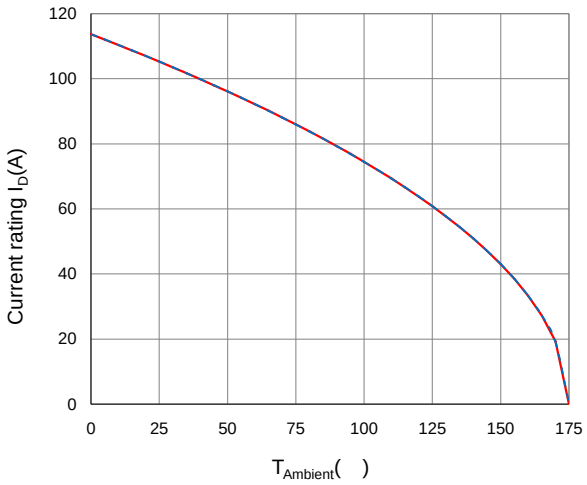
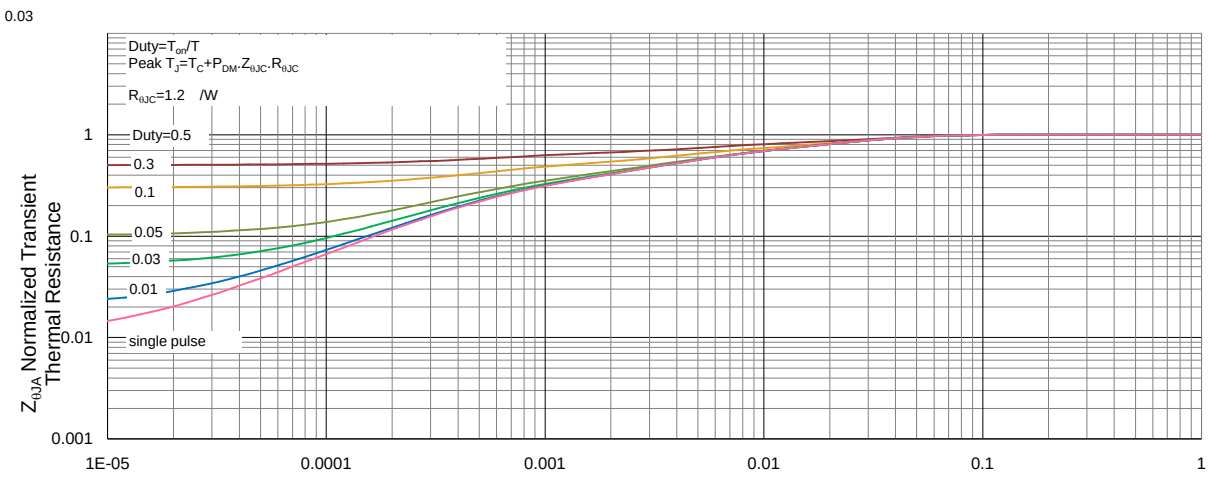
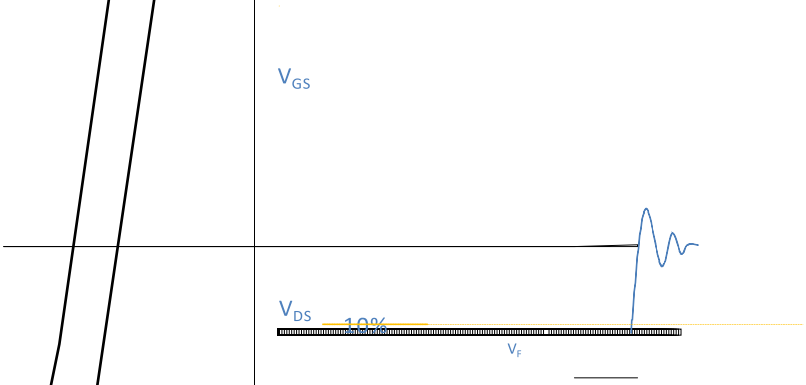


Figure 10. Maximun Drain Current vs. Case Temperature



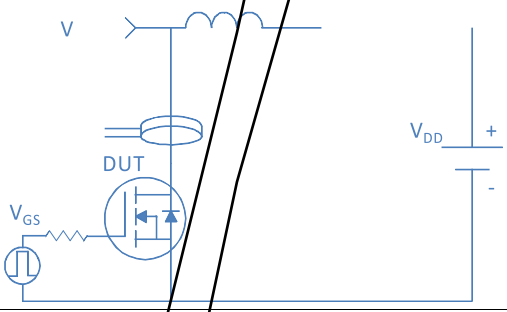


Inductive switching Test



Gate Charge Test

Uclamped Inductive Switching (UIS) Test



Diode Recovery Test

,

		9.97	10.28		
A2	9.80	10.00	10.72	0.45	4563 -1.58
D	4.30	4.50	4.70		
E	9.00	9.20	9.40		
G1	1.32	1.52	1.72		
G2	0.70	0.82	0.95		
G3	0.45	0.52	0.60		
H	3.50	3.60	3.70		
I	2.70	2.80	2.90		
J	15.70	15.97	16.25		
K	2.20	2.40	2.60		
L	1.15	1.27	1.40		
N	6.40	6.60	6.80		

TO-263, 2 leads

Symbol	Min	Nom	Max
A	9.66	9.97	10.28
B	1.02	1.17	1.32
C	8.59	9.00	9.40
D1	1.14	1.27	1.40
D2	0.70	0.83	0.95
D3		5.08	
E	15.09	15.24	15.39
F	1.15	1.28	1.40
G	4.30	4.50	4.70
H	2.29	2.54	2.79
I		0.25	
K	1.30	1.45	1.60
a1	0.45	0.55	0.65
a2(degree)	0°		8°